

Title (en)

FET and method for manufacturing such.

Title (de)

Feldeffekttransistor und Verfahren zu seiner Herstellung.

Title (fr)

Transistor à effet de champ et procédé pour sa fabrication.

Publication

EP 0059848 A2 19820915 (EN)

Application

EP 82100968 A 19820210

Priority

US 24067781 A 19810305

Abstract (en)

A field effect transistor and method of making the same are disclosed. A thick mesa (17) of dielectric material is grown on a semiconductor substrate (10) and two or more layers (20a, b; 28a, b) of polycrystalline silicon grown on the vertical sides of the mesa (17) serve a masking function to define the gate region of the transistor with high accuracy. The mesa (17) and the two or more polycrystalline layers (20a, b; 28a, b) remain in the final device.

IPC 1-7

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IPC 8 full level

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CPC (source: EP US)

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Cited by

EP0193117A3; US5994718A; US5486480A; US5893742A; US6091111A; WO9622615A1

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